

DS item
AQ.
~~///~~
(DS
filed
7/2/7)

PAT-NO: JP410301147A

DOCUMENT-IDENTIFIER: JP 10301147 A

TITLE: SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

PUBN-DATE: November 13, 1998

INVENTOR-INFORMATION:

NAME

YAMAZAKI, SHUNPEI

ONUMA, HIDETO

TAKANO, TAMAE

OTANI, HISASHI

ASSIGNEE-INFORMATION:

NAME

COUNTRY

SEMICONDUCTOR ENERGY LAB CO LTD

N/A

APPL-NO: JP09123284

APPL-DATE: April 25, 1997

INT-CL (IPC): G02F001/136, H01L027/04, H01L021/822, H01L029/786
, H01L021/336

ABSTRACT:

PROBLEM TO BE SOLVED: To provide a technique for embodying the simplification of processes for manufacturing semiconductor devices.

SOLUTION: An insulating film 103 having apertures 104, 105 is formed on an amorphous film 102 contg. silicon. Next, crystallization is executed by introducing catalyst elements from these apertures. Apertures 111 are formed at this insulating film 103 after the crystallization and P ions are added thereto. Regions 112, 113 for guttering the catalyst elements and regions 114 functioning afterward as lower electrodes of auxiliary capacitors may be simultaneously formed by this process.

COPYRIGHT: (C)1998,JPO